

Defects and disorder in apatite-type silicate oxide ion conductors: implications for conductivity

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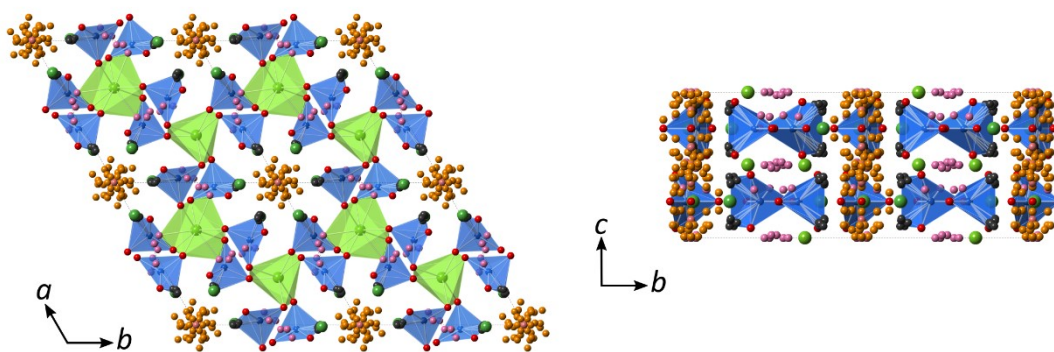


Figure S1. Illustrations of the interstitial sites that have been proposed in $La_{9,33+x}(SiO_4)_6O_{26+1.5x}$ including symmetry equivalents. Three main areas can be identified: near the SiO_4 groups coloured grey, between two SiO_4 groups coloured pink and within the O4 channel coloured orange.

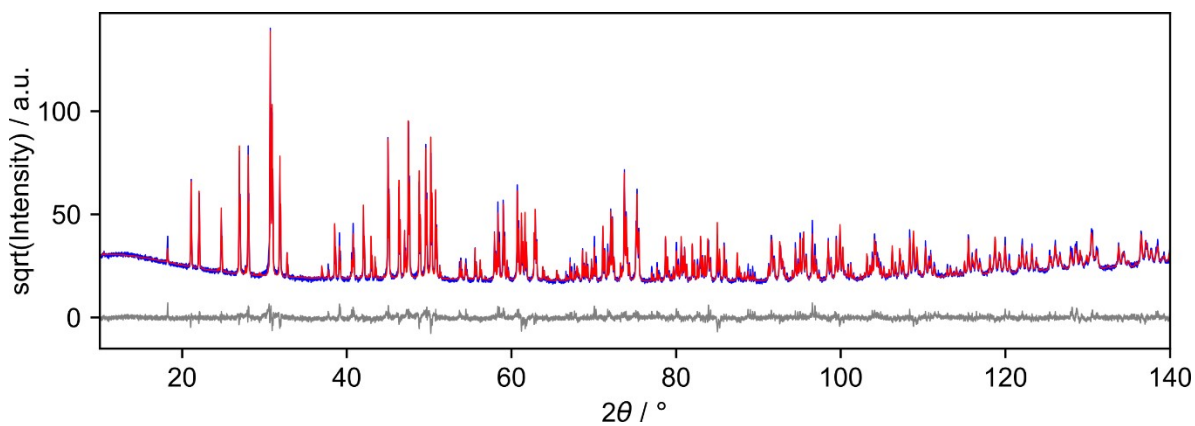


Figure S2. Rietveld refinement of crushed crystals of $La_{9,64}Si_{5,77}O_{26}$. $R_{wp} = 8.898\%$, $GOF = 2.27$.

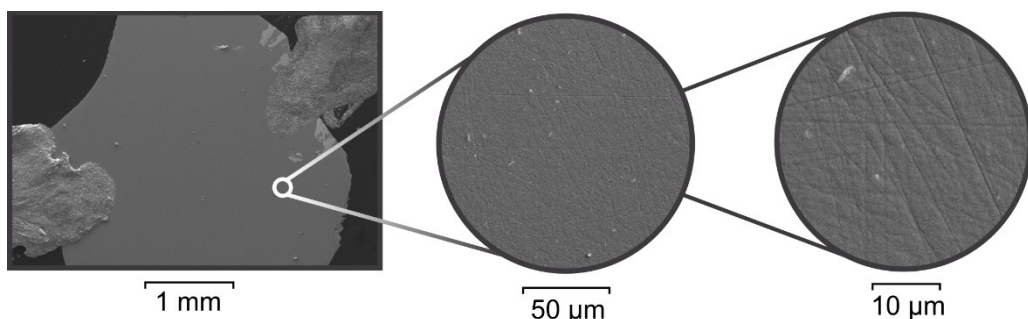


Figure S3. SEM micrographs of the polished LSO crystal. The gold paste used to prevent charge build-up is visible in the top right and bottom left corners. The micrographs in circles show progressively smaller length scales to show the homogeneity of the crystal. The lighter-coloured flecks result from the carbon coating and the straight lines from the polishing treatment.

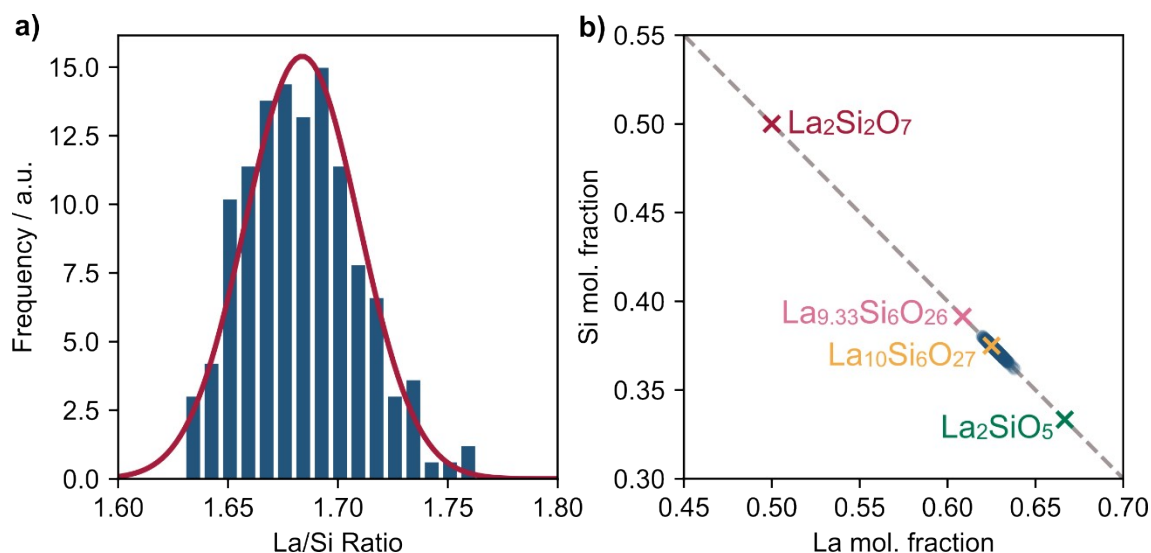


Figure S4. a) A histogram of the La:Si ratios measured by SEM-EDX, using 225 spectra from 5 different sites on a polished crystal of LSO, fitted with the red gaussian distribution. b) Compounds related to LSO expressed as Si and La mole fractions. The experimental mole fractions of LSO calculated from the histogram in a) are shown with blue shading. The nominal mole fractions of related compositions are marked on the graph for comparison.

The Gaussian fit to the histogram gives a mean La/Si ratio of 1.684(2) and a standard deviation of 0.026. This corresponds to $\text{La}_{9.67}\text{Si}_{5.74}\text{O}_{26}$, when normalised to O_{26} . To give an idea of the precision of this EDX technique, one standard deviation away from the mean in either direction corresponds to ratios of 1.710 and 1.658, which give the compositions $\text{La}_{9.73}\text{Si}_{5.75}\text{O}_{26}$ and $\text{La}_{9.61}\text{Si}_{5.79}\text{O}_{26}$, respectively. There is an approximate <1% difference in the Si content between the latter two compositions.

Specific gravity measurements

Due to the effects of buoyancy, crystals weigh less in ethanol than in air and the specific gravity can be calculated using

$$G_{crystal} = \frac{m_{air}}{m_{air} - m_{EtOH}} G_{EtOH} \quad \text{Eq. S1}$$

where m is the mass and G is the specific gravity (0.7893 g cm^{-3} for ethanol at $20 \text{ }^\circ\text{C}$). The density of the crystal is then $G_{\text{crystal}} \times \rho_{\text{water}}$, where ρ_{water} is the density of water. A simple apparatus to allow density measurements was mounted on a 4-decimal-place balance, as described by Brandriss¹. The experimental uncertainty was quantified by measuring the specific gravity of four materials with known density: quartz glass pieces, silicon wafers, and agate and zirconia milling balls; a summary of the standard measurements is given in Table S1. For quartz and silicon, the known density corresponds to the theoretical density, and for the milling balls, the density was measured using their mass and volume. For each material, between 6 and 15 different samples were measured. This confirmed the accuracy of the experiment and defined a typical standard deviation of 0.02 g cm^{-3} . The primary source of error is the precision of the balance, and scales as $1/\text{mass}$ of the crystal. Test measurements determined that the crystal must weigh more than 0.05 g to produce a meaningful measured density value. The specific gravities of four different pieces of the LSO (with masses 0.2878 , 0.1660 , 0.0897 and 0.0755 g) were each measured 20 times to provide an average density for the crystals.

Table S1. Comparison between the measured and known densities standard samples.

Standard	$\rho_{\text{known}} / \text{g cm}^{-3}$	$\rho_{\text{measured}} / \text{g cm}^{-3}$
Agate bead	2.60	2.585(3)
ZrO ₂ bead	6.05	6.066(3)
Si wafer	2.33	2.33(1)
Quartz glass	2.20	2.191(4)

Point	La content	Density / g cm^{-3}	Si content	O content
1	9.615	5.410	5.789	26
2	9.640	5.418	5.770	26
3	9.675	5.430	5.744	26
4	9.651	5.430	5.820	26.12
5	9.642	5.410	5.726	25.91

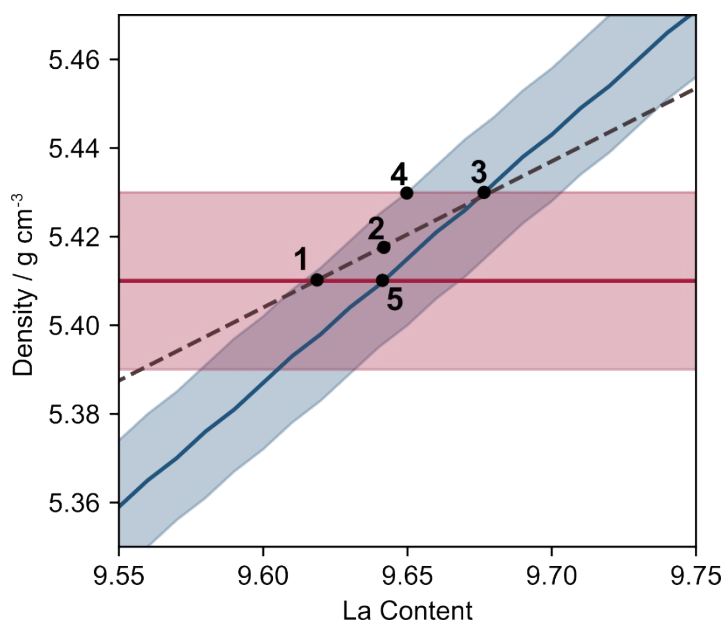


Figure S5. Zoom of Figure 2 in the main text showing the estimate of the final composition (point 2) and the upper and lower bounds of composition assuming oxygen stoichiometry (points 1 and 2). Shaded regions represent one standard

deviation away from the mean for the measured density (pink) and calculated density using $\text{La}_x\text{Si}_{x/1.684}\text{O}_{[3x+4(x/1.684)]/2}$. The dotted line indicates oxygen stoichiometric compositions, i.e. $\text{La}_x\text{Si}_{(52-3x)/4}\text{O}_{26}$.

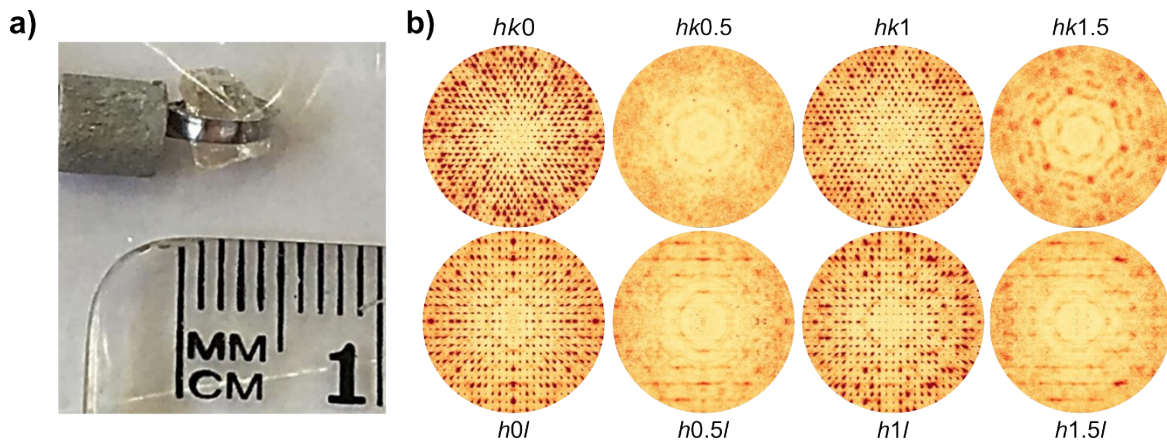


Figure S6. a) The crystal used for neutron diffraction measurement and b) example diffraction planes reconstructed from the neutron diffraction data collected on LSO at 40 K. Significant diffuse scatter is seen between the Bragg peaks.

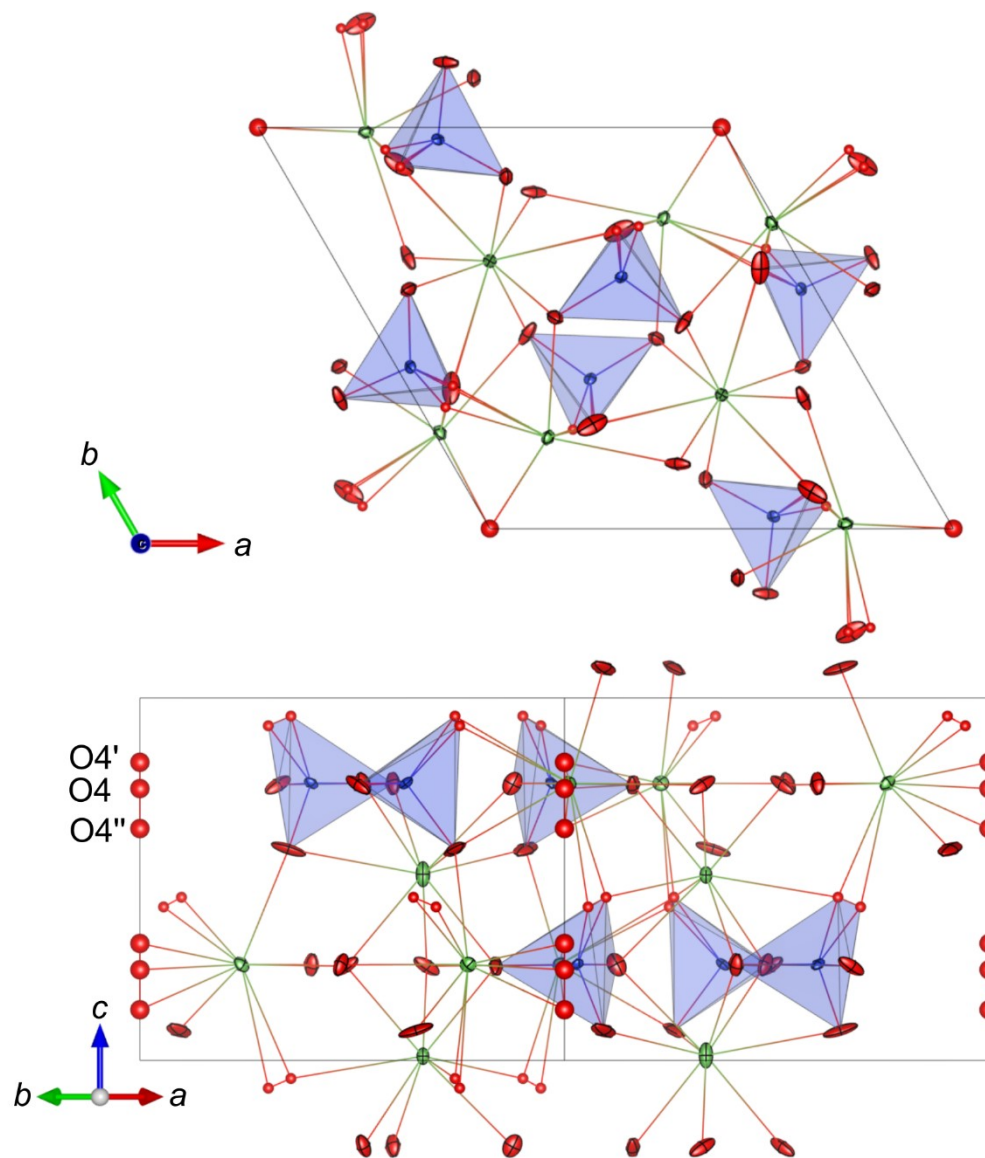


Figure S7. Final refined room temperature structure with ellipsoids drawn at 50% probability.

Table S2. Summary of single crystal neutron refinements for LSO at 40 and 295 K.

Temperature	40K	295K
Space group	$P6_3$	$P6_3$
$a / \text{\AA}$	9.7027(17)	9.7133(17)
$c / \text{\AA}$	7.1793(16)	7.1843(18)
$V / \text{\AA}^3$	585.33(16)	587.01(17)
# Reflections		
all	20874	10449
Observed ($>3\sigma$)	15339	7385
Excluded ($ F_{\text{obs}} - F_{\text{calc}} > 10\sigma$)	779	366
$R / \%$	7.72	6.92
$wR / \%$	6.81	6.23

Table S3. Refined structural parameters for $La_{9.64}Si_{5.77}O_{26}$.

Site	Occ.	x	y	z	$U_{iso} / \text{\AA}^2$	$U_{11} / \text{\AA}^2$	$U_{22} / \text{\AA}^2$	$U_{33} / \text{\AA}^2$	$U_{12} / \text{\AA}^2$	$U_{23} / \text{\AA}^2$	$U_{13} / \text{\AA}^2$	
295K												
La1_1	2b	0.841(6)	0.3333	0.6667	0.0118(2)	0.0112(5)	0.0106(7)	0.0106(7)	0.0123(6)	0.0053(4)	0	0
La1_2	2b	0.979(6)	0.6667	0.3333	0.0140(1)	0.0133(5)	0.0054(6)	0.0054(6)	0.0292(8)	0.0027(3)	0	0
La2	6c	1	0.22725(5)	-0.01205(4)	0.2639(2)	0.0086(1)	0.0010(1)	0.0062(1)	0.0092(1)	0.0037(1)	-0.0001(4)	0.0007(4)
Si1	6c	0.9617	0.40306(8)	0.37292(9)	0.2652(3)	0.0047(2)	0.0053(3)	0.0051(3)	0.0044(1)	0.0037(2)	-0.0017(7)	-0.0030(7)
O1	6c	1	0.32472(9)	0.48604(9)	0.2601(3)	0.0170(3)	0.0246(4)	0.0222(4)	0.0152(2)	0.0199(3)	0.0109(5)	0.0123(5)
O2	6c	1	0.59592(7)	0.47326(7)	0.2585(3)	0.0144(2)	0.0091(3)	0.0096(3)	0.0208(2)	0.0019(2)	-0.0006(7)	0.0048(7)
O3_1	6c	1	0.3495(3)	0.2579(2)	0.0773(2)	0.0238(6)	0.0487(11)	0.0209(6)	0.0089(3)	0.0228(7)	-0.0142(4)	-0.0088(3)
O3_2	6c	0.312(4)	0.3024(4)	0.2469(4)	0.4178(4)	0.0053(2)						
O3_2'	6c	0.688(4)	0.3559(2)	0.2581(2)	0.4446(2)	0.0053(2)						
O4	2a	0.4577(4)	0	0	0.2504(5)	0.0149(5)						
O4'	2a	0.349(4)	0	0	0.3218(7)	0.0149(5)						
O4''	2a	0.193(4)	0	0	0.1408(10)	0.0149(5)						
40K												
La1_1	2b	0.856(3)	0.3333	0.6667	0.0004(2)	0.0079(3)	0.0063(3)	0.0063(3)	0.0110(4)	0.0031(2)	0	0
La1_2	2b	0.964(3)	0.6667	0.3333	0.0030(1)	0.0098(2)	0.0027(3)	0.0027(3)	0.0241(5)	0.0013(1)	0	0
La2	6c	1	0.22732(3)	-0.01214(3)	0.2500(2)	0.00628(8)	0.00298(8)	0.00533(6)	0.00556(6)	0.00145(7)	0.0009(2)	-0.0009(2)
Si1	6c	0.9617	0.40311(5)	0.37280(5)	0.2496(3)	0.0036(1)	0.0052(1)	0.0040(1)	0.0027(1)	0.0031(1)	0.0001(4)	0.0006(4)
O1	6c	1	0.32482(6)	0.48629(6)	0.2527(3)	0.0129(1)	0.0183(2)	0.0189(2)	0.0109(1)	0.0163(2)	-0.0092(3)	-0.0108(3)
O2	6c	1	0.59642(5)	0.47338(5)	0.2452(3)	0.0096(1)	0.0064(1)	0.0056(1)	0.0139(1)	0.0009(1)	-0.0017(3)	0.0007(4)
O3_1	6c	1	0.3525(2)	0.2582(1)	0.0667(2)	0.0175(3)	0.0373(6)	0.0173(3)	0.0044(1)	0.0186(3)	-0.0107(2)	-0.0069(1)
O3_2	6c	0.306(4)	0.3024(2)	0.2463(2)	0.4124(3)	0.0050(3)						
O3_2'	6c	0.694(4)	0.3544(1)	0.2573(2)	0.4347(3)	0.0050(2)						
O4 0	2a	1	0	0	0.2399(13)	0.0674(9)	0.0099(3)	0.0099(3)	0.182(3)	0.0050(1)	0	0

Table S4. Refined bond lengths for La and Si polyhedra at 295 and 40 K. The distance between O3_2 and O3_2' is 0.50 Å at both temperatures, and at 295 K, the distances O4–O4', O4–O4'' and O4'–O4'' are 0.51, 0.79 and 1.30 Å, respectively.

295K		40K	
Bond	Bond Length / Å	Bond	Bond Length / Å
La1_1 – O1 (x3)	2.4737	La1_1 – O1 (x3)	2.5002
La1_1 – O2 (x3)	2.5343	La1_1 – O2 (x3)	2.5590
La1_1 – O3_2' (x3)	2.7751	La1_1 – O3_2' (x3)	2.7753
La1_1 – O3_2 (x3)	3.2622	La1_1 – O3_2 (x3)	3.2694
La1_2 – O1 (x3)	2.5035	La1_2 – O1 (x3)	2.4720
La1_2 – O2 (x3)	2.5470	La1_2 – O2 (x3)	2.5107
La1_2 – O3_1 (x3)	2.8023	La1_2 – O3_1 (x3)	2.7969
La2 – O4	2.2701	La2 – O4	2.2693
La2 – O4'	2.3059	La2 – O3_2'	2.4749
La2 – O4''	2.4344	La2 – O3_1	2.4769

La2 - O3_2'	2.4713	La2 - O3_2	2.4966
La2 - O3_1	2.4857	La2 - O3_2	2.5154
La2 - O3_2	2.5030	La2 - O2	2.5191
La2 - O3_2	2.5124	La2 - O3_2'	2.6250
La2 - O2	2.5221	La2 - O3_1	2.6271
La2 - O3_1	2.6305	La2 - O1	2.7703
La2 - O3_2'	2.6328	Si - O3_2	1.6122
La2 - O1	2.7729	Si - O1	1.6207
Si - O3_2	1.6022	Si - O2	1.6251
Si - O1	1.6197	Si - O3_1	1.6294
Si - O2	1.6231	Si - O3_2'	1.6480
Si - O3_1	1.6321		
Si - O3_2'	1.6443		

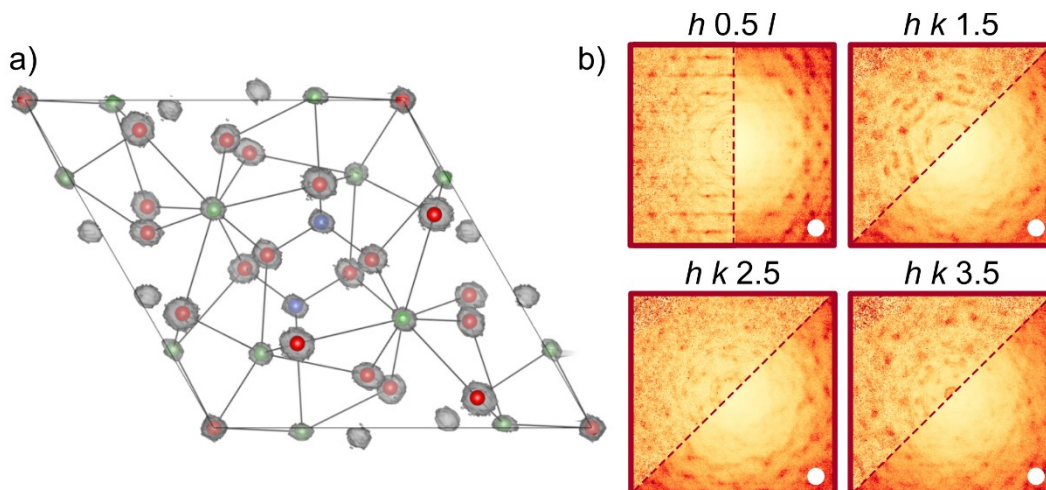


Figure S8. a) The large box model used to simulate diffuse scattering folded back down into a single unit cell. The green, blue and red spheres shows the average positions of La, Si and O, respectively, and the grey clouds encompass the positions of all the atoms in the supercell. b) Selected experimental and simulated diffuse scattering $h k l$ sections. Calculated patterns are indicated with a white circle and the dividing line between calculated and experimental patterns is shown by a red dashed line. Intensities of the calculated patterns are arbitrary and are coloured to match the experimental patterns.

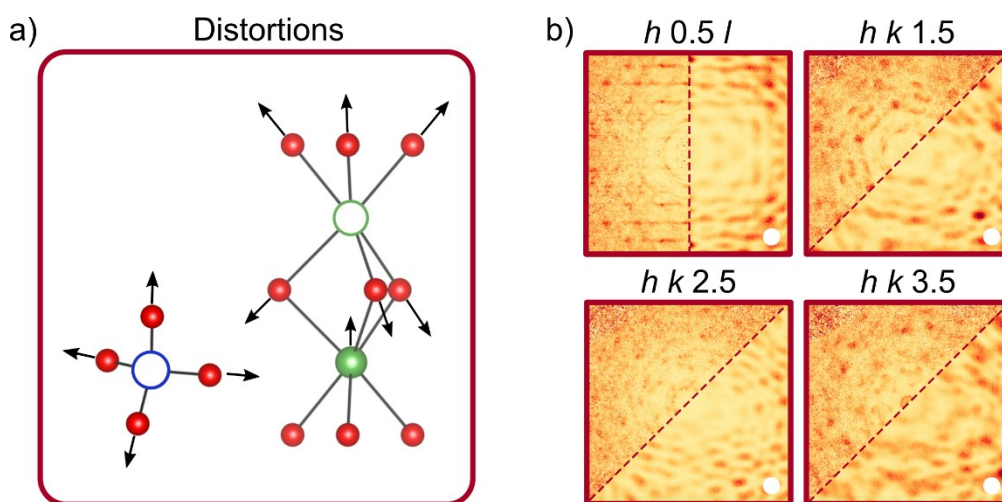


Figure S9. a) Breathing distortions around Si (blue circle) and La vacancies (green circle); note that the arrows are not to scale. b) The resulting calculated diffuse scattering and corresponding experimental sections.

Modelling O4 displacement correlations

O4 atoms were distributed across the three sites identified from the RT refinement, as shown in Figure S10a, with the central atom at fractional coordinates $(0, 0, 0.25)$ and the other two shifted up or down along the c -axis to $(0, 0, 0.35)$ and $(0, 0, 0.15)$. The occupancies of these three sites from the structure refinement suggest that the central position is occupied $\sim 50\%$ of the time. For simplicity in this model, the remaining 50% of atoms was distributed over the upper and lower sites equally.

An Ising-like energy function can be employed to allow different correlations in the O4 positions to be created. The three sites were assigned a pseudo-spin value of -1, 0 and 1 for lower, central and upper sites, respectively. A Monte Carlo ordering algorithm was written to swap O4 atoms with different spins and calculate the energies of the two configurations according to

$$E_i = \sum_{j=1}^n -k_{ij}\sigma_i\sigma_j \quad \text{Eq. S2}$$

where E_i is the energy of atom i , k_{ij} is the force constant between O4 atom i and its O4 neighbour j , σ_i is the assigned spin of atom i and n is the number of neighbours of atom i . To clarify, for this section of the modelling, the neighbours of atom i refer to its neighbouring O4 atoms even though they are nominally non-bonded. Each O4 has eight neighbours: six in the ab -plane, one above it, and one below. The starting force constant matrix was defined arbitrarily to make like spins have a weak interaction, opposite spins have a strong interaction, and spins of 0 to have no interactions. This definition was found by trial and error to give the desired ordering patterns.

A correlation between spins can be used to quantify the ordering patterns produced by the algorithm. After each MC cycle, the correlation is calculated by

$$\text{corr} = \frac{\sum \sigma_i\sigma_j}{n} \quad \text{Eq. S3}$$

For like spins, $\sigma_i\sigma_j = 1$, so if atom i is completely surrounded by like spins, $\text{corr} = 1$. If all the spins are opposing, $\text{corr} = -1$. A correlation can, therefore, be specified to define the type of ordering desired. The force constants are then scaled by the difference between the calculated and desired correlation value at the end of each MC cycle. Using this method, the O4 positions can be correlated separately in the ab -plane and along the c -axis with the sum in Equation S2 running over the two neighbours above and below the plane, or the six neighbours in the ab -plane, respectively. Example configurations are given in Figures S10b and S10c, where yellow, red and blue spheres represent O4 atoms in the lower, central and upper positions from Figure S10a. The configuration in S10b has a correlation of 0.35 parallel to the c -axis and 0.0 in the ab -plane, so like spins are clustered along the c -axis and are randomly distributed in the ab -plane. Note that a correlation significantly higher than 0.35 is not possible in this model as the three different spins necessitate that some neighbour interactions are not between like spins, so the overall correlation decreases. In the final model, these correlations translate to O4 atoms with the same vertical displacement being clustered together along c , approximating the correlated displacements that would result from electrostatics in a real material. The corresponding anti-correlation, where adjacent O4s prefer to be displaced in opposite directions, would model the effects of elastic strain in the LSO crystal.

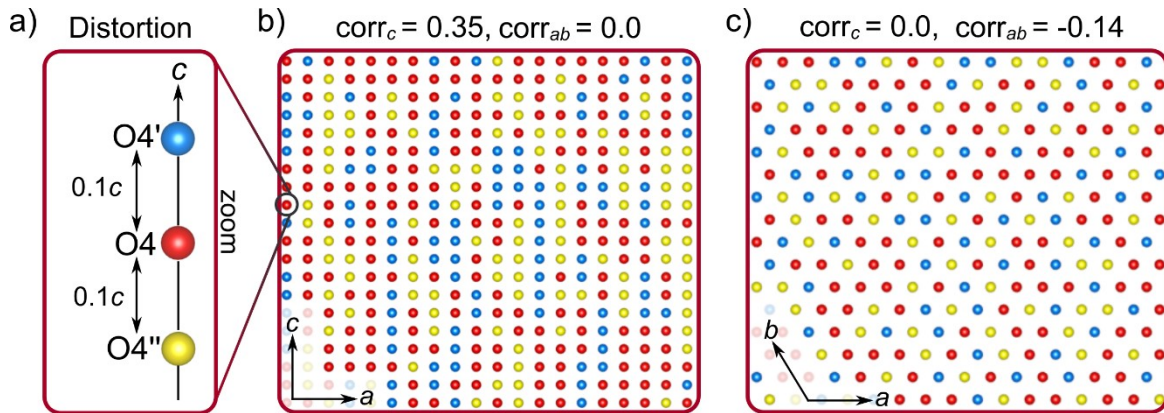


Figure S10. a) Modelling of the disorder on the O4 site. For each O4 in the supercell, the atom was placed on one of the positions indicated by the coloured spheres with 50% on the central position and 25% on the other two. b, c) Example configurations of the supercell showing only the O4 atoms to show the different ordering patterns produced. The colours correspond to the positions in a.

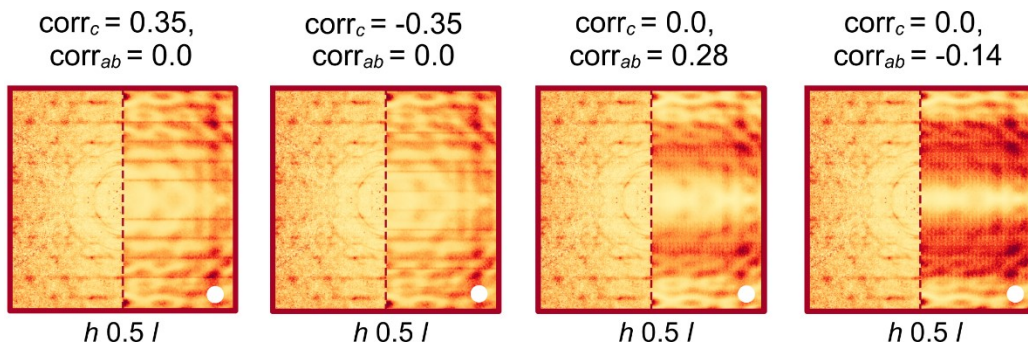


Figure S11. Diffuse scattering patterns produced by different correlations of O4 positions and the corresponding experimental patterns.

1 E. Brandriss, Mark, *J. Geosci. Educ.*, 2010, **58**, 155–165.